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Notice of Allowability	Application No.	Applicant(s)	
	10/619,581	RHEE ET AL.	
	Examiner	Art Unit	
	Walter L. Lindsay, Jr.	2812	
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	is (OR REMAINS) CLOSED in this ap) or other appropriate communication (IGHTS. This application is subject to 3 and MPEP 1308.	plication. If not included not will be mailed in due course. THIS	ive
1. This communication is responsive to Response filed 11/16	<u>5/2004</u> .		
2. X The allowed claim(s) is/are <u>13-30</u> .			
3. \boxtimes The drawings filed on <u>16 November 2004</u> are accepted by	the Examiner.		
4. Acknowledgment is made of a claim for foreign priority u a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be subn INFORMAL PATENT APPLICATION (PTO-152) which giv 6. CORRECTED DRAWINGS (as "replacement sheets") mu (a) including changes required by the Notice of Draftsper 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in 7. DEPOSIT OF and/or INFORMATION about the depondant of the proper included in the proper included in the proper included inc	e been received. e been received in Application No comments have been received in this of this communication to file a reply MENT of this application. nitted. Note the attached EXAMINER res reason(s) why the oath or declara set be submitted. rson's Patent Drawing Review (PTO - r's Amendment / Comment or in the of 1.84(c)) should be written on the drawithe header according to 37 CFR 1.1216 Dosit of BIOLOGICAL MATERIAL	national stage application from the complying with the requirements I'S AMENDMENT or NOTICE OF ation is deficient. -948) attached Office action of the back) of (d). must be submitted. Note the	
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Attachment(s) 1. Notice of References Cited (PTO-892)	5. Notice of Informal I	Patent Application (PTO-152)	
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Summary Paper No./Mail Da		
3. Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date	/08), 7 🔲 Examiner's Amend	ment/Comment	
4. Examiner's Comment Regarding Requirement for Deposit	8. ☑ Examiner's Statem 9. ☐ Other	ent of Reasons for Allowance	
of Biological Material	a. [] Otriel	STACY A WHITMORE PRIMARY EXAMINER	
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DETAILED ACTION

Allowable Subject Matter

1. Claims 13-21 are allowed.

2. The following is an examiner's statement of reasons for allowance: the prior art, either singly or in combination fails to anticipate or render obvious, the limitations of:

...depositing a lower poly-SiGe layer having a columnar crystalline structure over the gate insulating layer;

depositing an amorphous Si layer over the lower poly-SiGe layer; and crystallizing the amorphous Si layer to obtain an upper poly-Si layer having a random crystalline structure, as required by claim 13;

...depositing at least one intermediate layer having an amorphous structure over the lower poly-SiGe layer;

depositing an amorphous Si layer over the at least one intermediate layer; and crystallizing the amorphous Si layer to obtain an upper poly-Si layer having a random crystalline structure, as required by claim 22;

... depositing an amorphous intermediate layer over the lower poly-SiGe layer; depositing an upper poly-Si layer over the amorphous intermediate layer; and crystallizing the amorphous intermediate layer to obtain a crystallized intermediate layer having a random crystalline structure between the lower poly-SiGe layer and the upper poly-Si layer, as required by claim 30.

Additionally claim 13 is allowed in view of the information provided in first paragraph and second paragraph of page 3, pertaining to paragraphs [0085], [0090]

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and [0095] of the specification which, give reasons to expect results not common to prior art annealing processes of amorphous silicon.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Walter L. Lindsay, Jr. whose telephone number is (571) 272-1674. The examiner can normally be reached on Monday-Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John F Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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